## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

## LISTING OF CLAIMS:

1. (currently amended): A laser apparatus comprising:

a semiconductor laser element which emits first laser light having a first wavelength;

a surface-emitting semiconductor element which is excited with said first laser light, emits second laser light having a second wavelength which is longer than said first wavelength, and has an active layer and a first mirror arranged on one side of said active layer; said surface-emitting semiconductor being excited with said first laser light;

a second mirror which is arranged outside said surface-emitting semiconductor element so that said first and second mirrors form a resonator in-which said second laser light resonates oscillates second laser light having a second wavelength which is longer than said first wavelength; and

a modulation unit which modulates a gain of said active layer said surface emitting semiconductor element;

wherein said second mirror is physically separated from said surface-emitting semiconductor element by an air gap.

2. (currently amended): A laser apparatus according to claim 1, wherein said surface-emitting semiconductor element has a pn junction, and said modulation unit modulates <u>said gain</u> of said active layer the surface emitting semiconductor element by varying a voltage applied to the pn junction.

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- 3. (currently amended): A laser apparatus according to claim 1, wherein said surface-emitting semiconductor element has a Schottky junction, and said modulation unit modulates said gain of said active layer the surface emitting semiconductor element by varying a voltage applied to the Schottky junction.
- 4. (original): A laser apparatus according to claim 1, wherein said surface-emitting semiconductor element comprises a structure for controlling a spatial mode of said second laser light.
- 5. (currently amended): A laser apparatus according to claim 4, wherein said structure is realized by a pinhole spatial filter being arranged at a light-exit end surface of said surface-emitting semiconductor element, having a pinhole, and allowing passage of said second laser light omitted by the surface emitting semiconductor element, through only the pinhole.
- 6. (currently amended): A laser apparatus according to claim 4, wherein <u>said structure is</u>

  <u>realized</u> by said first mirror <u>which</u> has a limited area, <u>and</u> is arranged in parallel with a light-exit

  end surface of said surface-emitting semiconductor element., and realizes said structure.
- 7. (currently amended): A laser apparatus according to claim 4, wherein <u>said structure is</u>

  <u>realized</u> by said active layer <u>which</u> is formed in only a limited area in a plane parallel to a lightexit end surface of said surface-emitting semiconductor element. <u>and realizes said structure.</u>
- 8. (original): A laser apparatus according to claim 4, wherein said structure has a size which is 0.1 to 10 times as large as a diameter to which said second laser light spreads at a position of the structure for controlling the spatial mode of the second laser light.

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- 9. (previously presented): The laser apparatus according to claim 1, wherein said first laser light enters said resonator from a first surface of said first mirror which is opposite the active layer to excite the surface-emitting semiconductor element.
  - 10. (canceled).
- 11. (previously presented): The laser apparatus according to claim 1, wherein said first laser light enters said surface-emitting semiconductor element through said air gap.
  - 12. (canceled).
  - 13. (canceled).